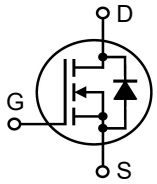
IXYS

X4-Class Power MOSFET™

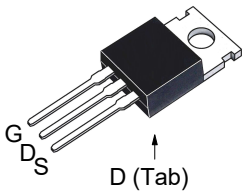
IXTP94N20X4

V_{DSS} = 200V
I_{D25} = 94A
$R_{DS(on)}$ ≤ 10.6mΩ

N-Channel Enhancement Mode
Avalanche Rated



TO-220 (IXTP)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 175°C	200	V
V_{DGR}	T_J = 25°C to 175°C, R_{GS} = 1MΩ	200	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	94	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	220	A
I_A	T_C = 25°C	47	A
E_{AS}	T_C = 25°C	1	J
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	20	V/ns
P_D	T_C = 25°C	360	W
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +175	°C
T_L	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	°C
M_d	Mounting Torque	1.13 / 10	Nm/lb.in
Weight		3	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	200			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	2.5		4.5	V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			20	μA
	T_J = 150°C			500	μA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Note 1			10.6	mΩ

Features

- International Standard Package
- Low $R_{DS(ON)}$ and Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
g_{fs}	V_{DS} = 10V, I_D = 0.5 • I_{D25}, Note 1	60	100		S
R_{Gi}	Gate Input Resistance		5.3		Ω
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		5050		pF
C_{oss}			750		pF
C_{rss}			4		pF
	Effective Output Capacitance				
$C_{o(er)}$	Energy related; V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		390		pF
$C_{o(tr)}$	Time related; V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		1670		pF
$t_{d(on)}$	**Resistive Switching Times**		18		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		9		ns
$t_{d(off)}$	R_G = 5Ω (External)		97		ns
t_f			7		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		77		nC
Q_{gs}			21		nC
Q_{gd}			25		nC
R_{thJC}				0.42	°C/W
R_{thCS}			0.50		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
I_S	V_{GS} = 0V			94	A
I_{SM}	Repetitive, pulse Width Limited by T_{JM}			376	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.4	V
t_{rr}	I_F = 47A, -di/dt = 200A/μs		130		ns
Q_{RM}	V_R = 100V		1.1		μC
I_{RM}			17.0		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

Littelfuse reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123B1 6,306,728B1 6,404,065B1 6,534,343 6,583,505 6,683,344 6,710,405B2 6,710,463 6,727,585 6,759,692 6,771,478B2 7,005,734B2 7,063,975B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

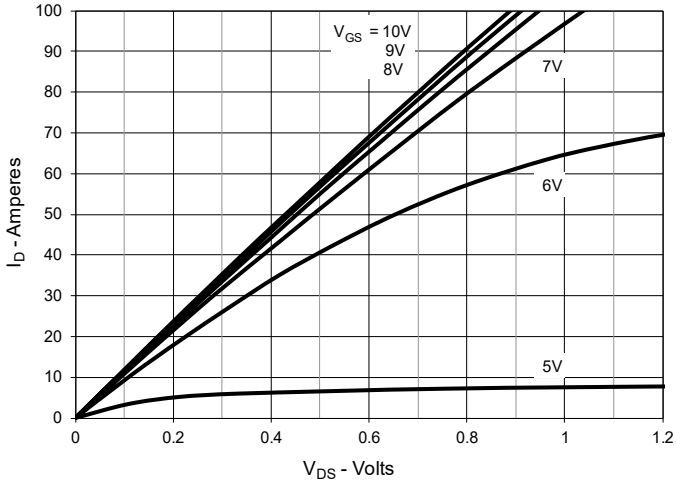


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

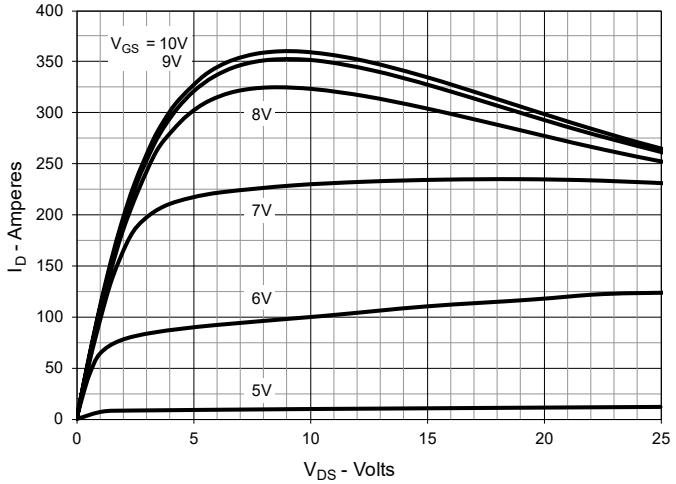


Fig. 3. Output Characteristics @ T_J = 150ºC

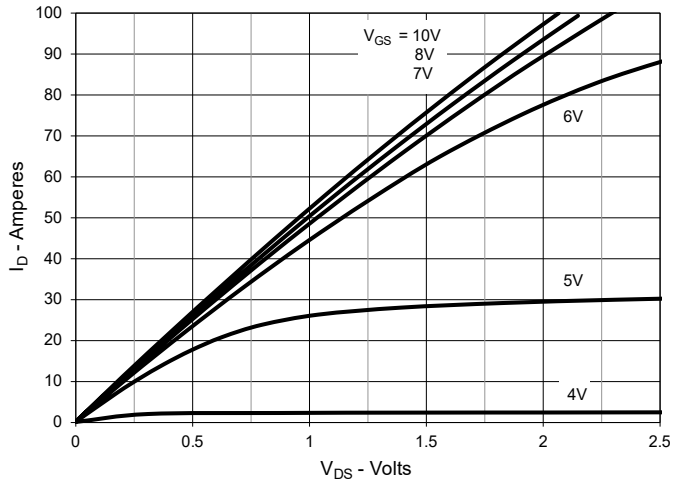


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 47A Value vs. Junction Temperature

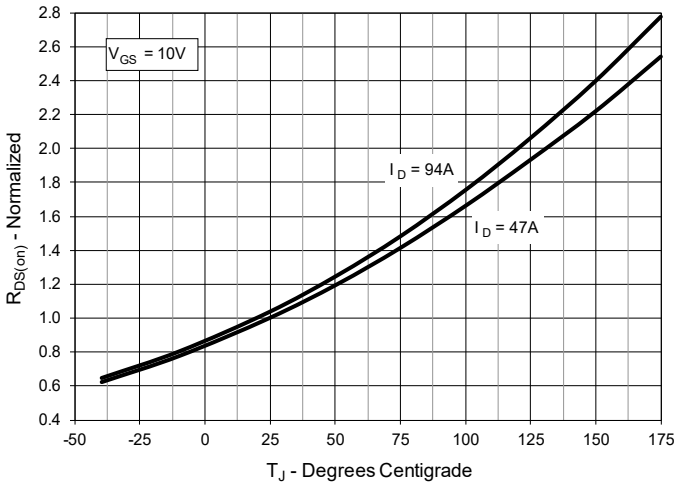


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 47A Value vs. Drain Current

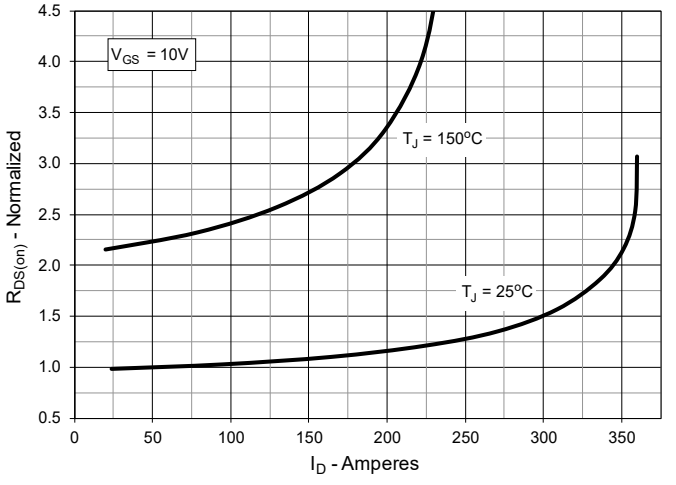
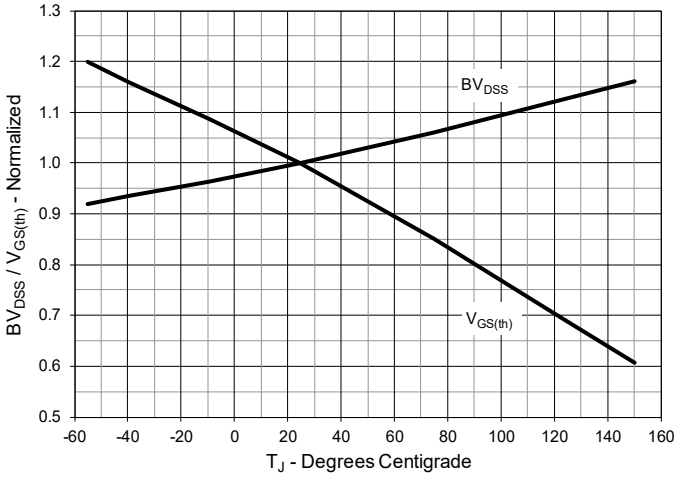


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature



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Fig. 7. Maximum Drain Current vs. Case Temperature

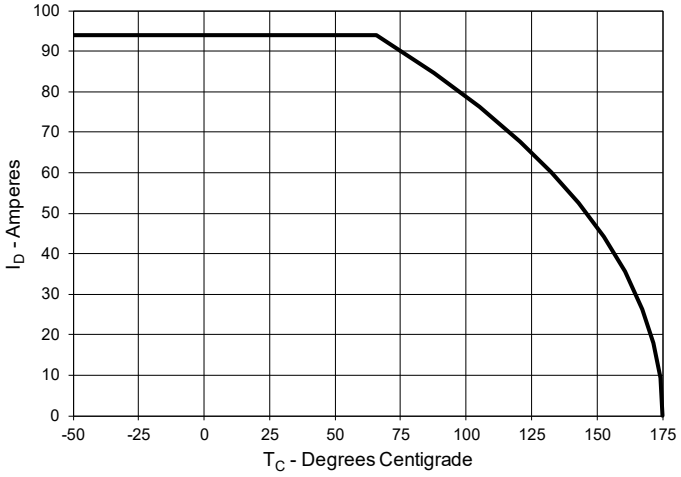


Fig. 8. Input Admittance

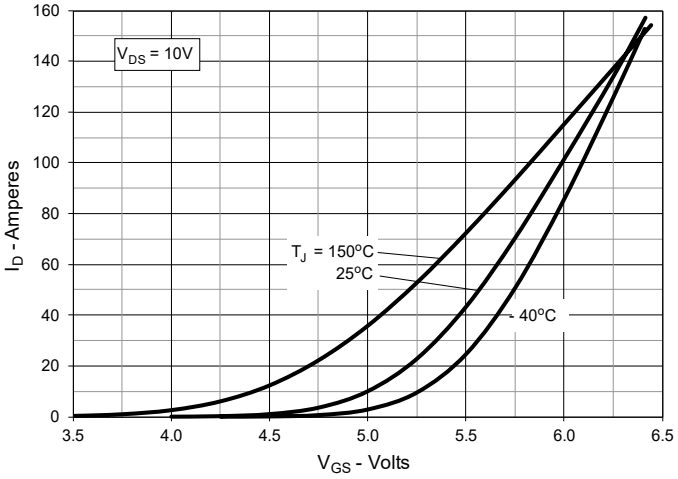


Fig. 9. Transconductance

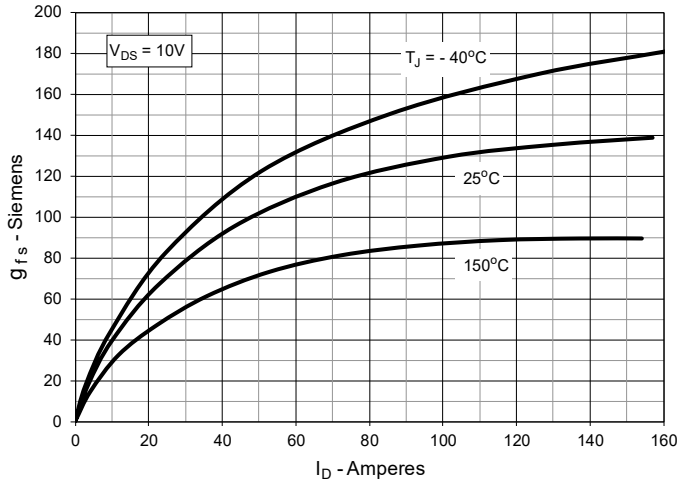


Fig. 10. Forward Voltage Drop of Intrinsic Diode

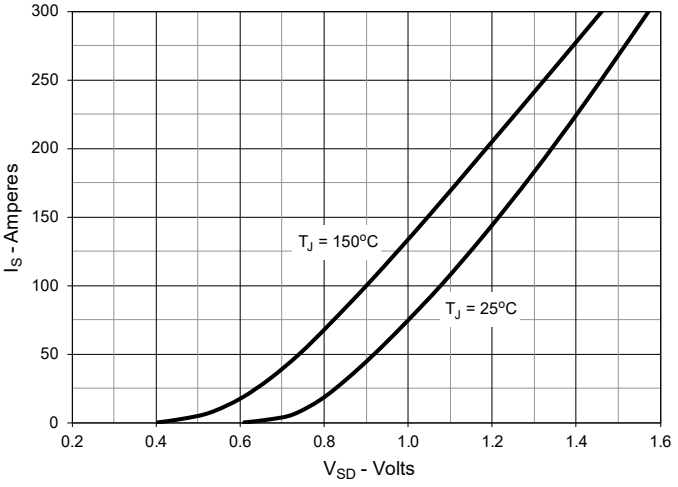


Fig. 11. Gate Charge

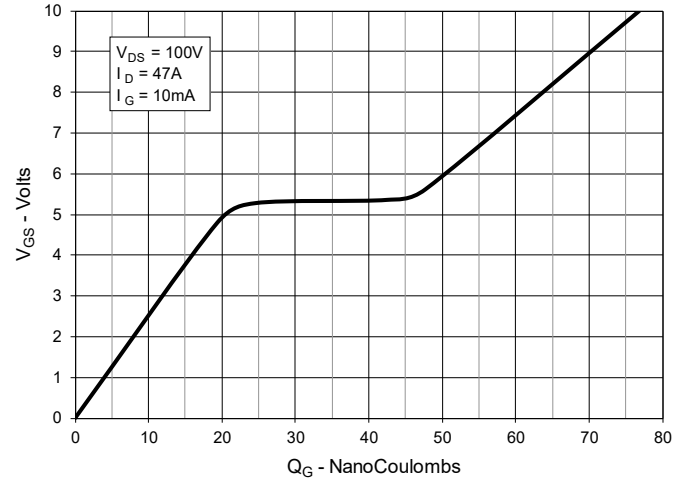
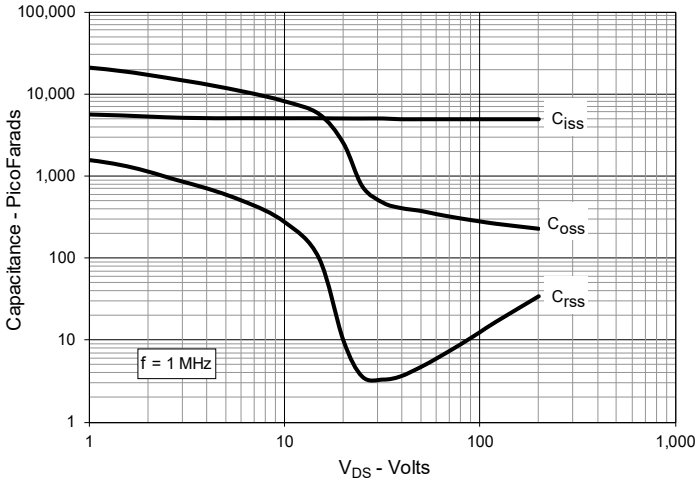


Fig. 12. Capacitance



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Fig. 13. Output Capacitance Stored Energy

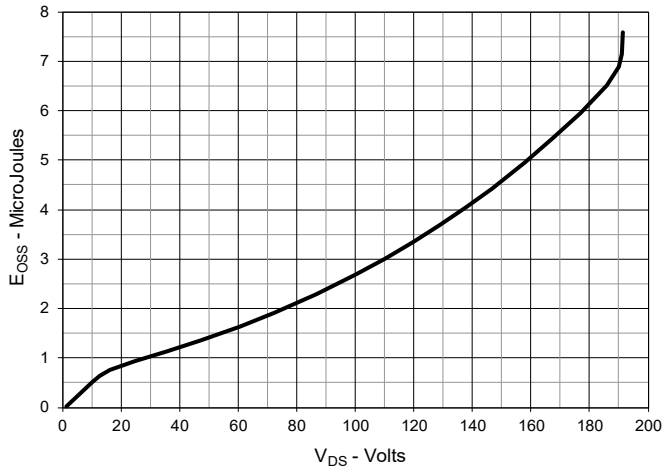


Fig. 14. Forward-Bias Safe Operating Area

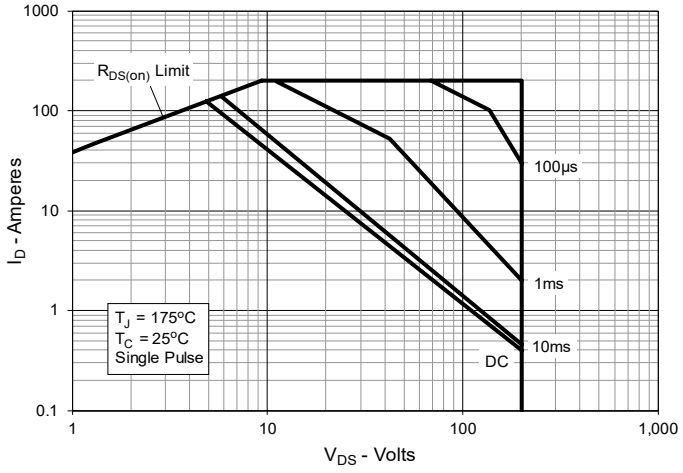
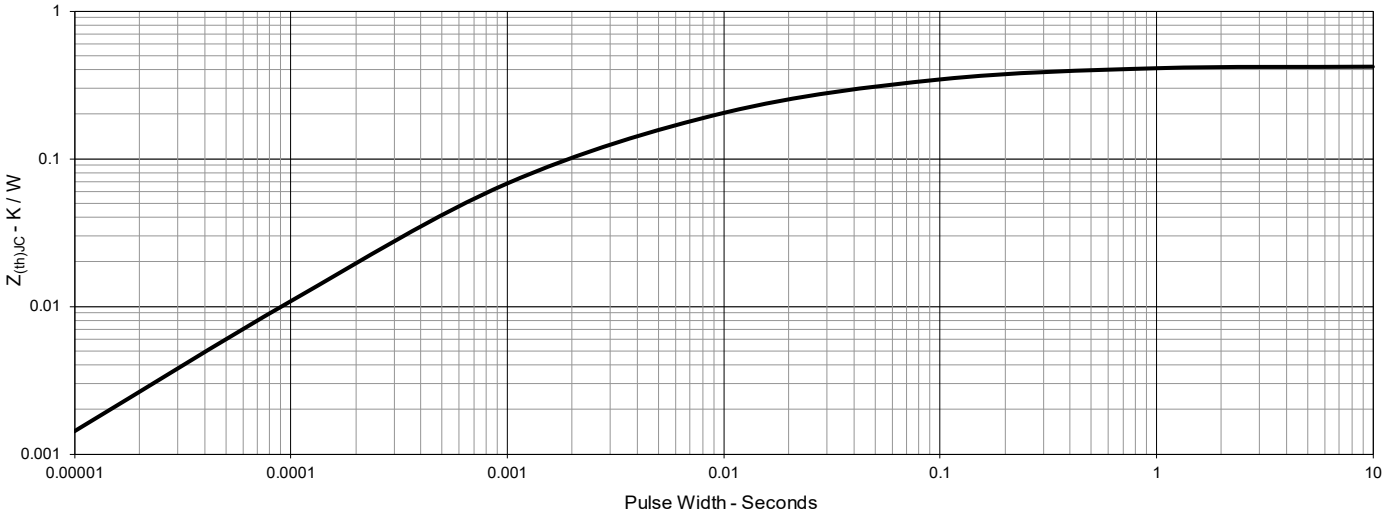
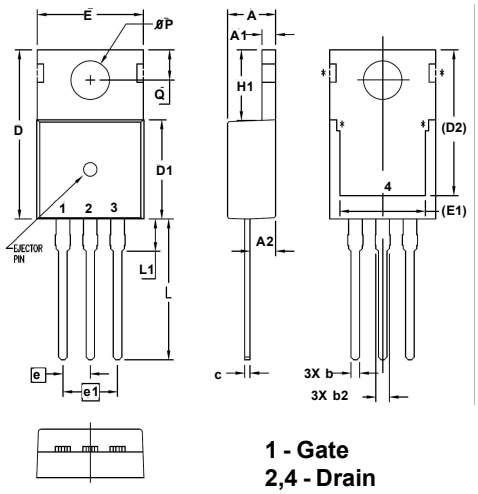


Fig. 15. Maximum Transient Thermal Impedance



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TO-220 Outline



1 - Gate
2,4 - Drain
3 - Source

SYM	INCHES		Millimeters	
	MIN	MAX	MIN	MAX
A	0.169	0.185	4.30	4.70
A1	0.047	0.055	1.20	1.40
A2	0.079	0.106	2.00	2.70
b	0.024	0.039	0.60	1.00
b2	0.045	0.057	1.15	1.45
c	0.014	0.026	0.35	0.65
D	0.587	0.626	14.90	15.90
D1	0.335	0.370	8.50	9.40
(D2)	0.500	0.531	12.70	13.50
E	0.382	0.406	9.70	10.30
(E1)	0.283	0.323	7.20	8.20
e	0.100 BSC		2.45 BSC	
e1	0.200 BSC		5.08 BSC	
H1	0.244	0.268	6.20	6.80
L	0.492	0.547	12.50	13.90
L1	0.110	0.154	2.80	3.90
ØP	0.134	0.150	3.40	3.80
Q	0.106	0.126	2.70	3.20

IXYS
A Littelfuse Technology

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